

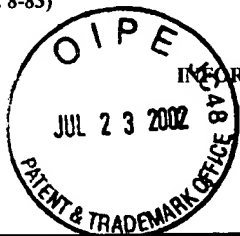
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INFORMATION DISCLOSURE CITATION

Page 1 of 1

APPLICANT(S)

William E. Hoke et al.

FILING DATE

February 14, 2000

GROUP

2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE*
<i>nm</i>	5 1 4 0 3 8 6	08/18/1992	Huang et al.			
<i>nm</i>	5 2 8 5 0 8 7	02/08/1994	Narita et al.			
<i>nm</i>	5 4 3 6 4 7 0	07/25/1995	Nakajima			
<i>nm</i>	5 5 0 4 3 5 3	04/02/1996	Kuzuhara			
<i>nm</i>	5 5 5 0 3 8 8	08/27/1996	Haruyama			
<i>nm</i>	5 5 9 6 2 1 1	01/21/1997	Onda et al.			
<i>nm</i>	5 6 4 1 9 7 7	06/24/1997	Kanamori			
<i>nm</i>	5 8 1 1 8 4 3	09/22/1998	Yamamoto et al.			
<i>nm</i>	6 1 4 4 0 4 8	11/07/2000	Suemitsu et al.			
<i>nm</i>	6 1 4 4 0 4 9	11/07/2000	Onda			
<i>nm</i>	6 2 5 8 6 3 9	07/10/2001	Rohdin et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	Country	Name	CLASS	SUBCLASS	TRANSLATION
						YES NO
<i>nm</i> JP7193224 (ABSTRACT)	07/28/1995	Japan				

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)

<i>nm</i>	P. Ho et al.; "Extremely High Gain, Low Noise InAl/As/InGaAs HEMTs Grown By Molecular Beam Epitaxy"; IEEE; 1998; pp. 184-186.
<i>nm</i>	Tom P.E. Broekaert et al.; "AlAs Etch-Stop Layers for InGaAlAs/InP Heterostructure Devices and Circuits"; IEEE; March 1992; Vol. 39, No. 3; pp. 533-536.
Examiner	<i>Kupla</i> Date Considered: <i>9-11-02</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and considered. Include copy of this form with next communication to applicant.	

(702143)

Donghee Kang